



## DataSheet: OCXO 80MHz

P/N: C2020-C200C1-80M000

### 1 ELECTRICAL SPECIFICATION

PARAMETER		CHARACTERISTIC
Output	Nominal Frequency	80 MHz
	Waveform	Sine Wave
	Level	≥ 8 dBm (25°C±5°C)
	Harmonics	≤ -30 dBc (25°C±5°C)
	Spurious	≤ -75 dBc (25°C±5°C)
Frequency Stability	Vs. Temperature	± 0.2ppm ( -55°C~+85°C, referred to +25°C)
	Vs. Load	± 5ppb ( Max ) (50Ω ± 5%, 25°C±5°C)
	Vs. Supply Changes	± 5ppb ( Max ) ( VDC ± 5%, 25°C±5°C)
	Vs. Ageing Per Year	± 0.1x10 <sup>-6</sup> (after 30 working days, typical)
Phase Noise	10Hz	-100dBc/Hz
	100Hz	-130dBc / Hz
	1kHz	-160dBc / Hz
	10kHz	-165dBc / Hz
	100kHz	-168dBc / Hz
Electrical Tuning Range		≥ ± 0.5ppm ( 0 ~ 5V, positive slope )
Freq. Control Input Impedance		≥ 100 kΩ
Startup Time (Output 8 dBm after Power Applied)		300ms over -40°C~+85°C
Crystal Type		SC
Input Power	Voltage	+12 VDC ±5%
	Warm-up State	≤ 3 W (25°C)
	Steady State	≤ 1.2 W (25°C)
Operation Temperature		-55°C~85°C
Storage Temperature		-55°C~105°C

### 2. ENVIRONMENTAL CONDITIONS

Humidity	GJB360B-2009, Method 103, Condition B (+40 °C ± 2 °C ; 90%~95%R.H.; non-condensing, 96 hours)
Storage Temperature	-55°C~+105°C
Vibration (non-operation)	GJB360B-2009, Method 201 (0.75mm total p-p, 10Hz~55Hz)
Shock (non-operation)	GJB360B-2009, Method 213, Condition J (30g, 11ms, half-sine)



### 3. PACKAGE

